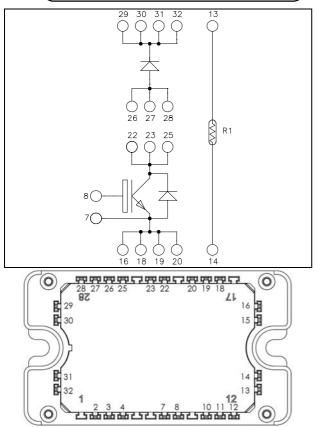


Boost chopper Trench + Field Stop IGBT3 Power Module



Pins 29/30/31/32 must be shorted together Pins 26/27/28/22/23/25 must be shorted together to achieve a phase leg Pins 16/18/19/20 must be shorted together

## $V_{CES} = 600V$ $I_{C} = 200A$ @ $T_{C} = 100^{\circ}C$

### Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

#### Features

#### • Trench + Field Stop IGBT3

- Low voltage drop
- Low tail current
- Switching frequency up to 20 kHz
- Low leakage current
- RBSOA and SCSOA rated
- Very low stray inductance
- Kelvin emitter for easy drive
- Internal thermistor for temperature monitoring
- AlN substrate for improved thermal performance

#### Benefits

- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

### All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

#### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit	
V <sub>CES</sub>	Collector - Emitter Voltage		600	V
I <sub>C</sub>	Continuous Collector Current	$T_C = 25^{\circ}C$	290	
		$T_{\rm C} = 100^{\circ}{\rm C}$	200	Α
I <sub>CM</sub>	Pulsed Collector Current	$T_C = 25^{\circ}C$	400	
V <sub>GE</sub>	Gate – Emitter Voltage		±20	V
PD	Power Dissipation	$T_C = 25^{\circ}C$	750	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	400A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

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### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
I <sub>CES</sub>	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.5	1.9	V
V <sub>CE(sat)</sub>		$I_C = 200A$	$T_j = 150^{\circ}C$		1.7		v
V <sub>GE(th)</sub>	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 2 \text{ mA}$		5.0	5.8	6.5	V
I <sub>GES</sub>	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

## **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			12.3		
Coes	Output Capacitance				0.8		nF
Cres	Reverse Transfer Capacitance	f = 1MHz			0.4		
$Q_{G}$	Gate charge	$V_{GE} = \pm 15V$ ; $V_{CE} = 300V$ $I_C = 200A$			2.2		μC
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switc	hing (25°C)		115		
Tr	Rise Time	$V_{GE} = \pm 15V$			45		
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{Bus} = 300V$ $I_{C} = 200A$			225		ns
$T_{\mathrm{f}}$	Fall Time	$R_G = 2\Omega$		55			
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 200A$ $R_G = 2\Omega$			130		
Tr	Rise Time				50		ns
T <sub>d(off)</sub>	Turn-off Delay Time				300		
T <sub>f</sub>	Fall Time				70		
Eon	Turn on Energy	$V_{GE} = \pm 15V$	$T_j = 25^{\circ}C$		1		mJ
Lon	Turn on Energy	$V_{Bus} = 300V$	$T_j = 150^{\circ}C$		1.8		1115
Б	Trans off Francisco	$I_C = 200A$	$T_j = 25^{\circ}C$		5.7		I
E <sub>off</sub>	Turn off Energy	$R_G = 2\Omega$	$T_j = 150^{\circ}C$		7		mJ
Isc	Short Circuit data	$V_{GE} \le 15V$ ; $V_{Bus} = 360V$ $t_p \le 6\mu s$ ; $T_j = 150^{\circ}C$			1000		А
$R_{thJC}$	Junction to Case Thermal Resistance					0.20	°C/W

## Chopper diode ratings and characteristics

Symbol	Characteristic Test Conditions			Min	Тур	Max	Unit
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage					600	V
I <sub>RM</sub>	Reverse Leakage Current	$V_R=600V$				250	μA
I <sub>F</sub>	DC Forward Current		$Tc = 80^{\circ}C$		200		Α
$V_{\rm F}$	Diode Forward Voltage	$I_F = 200A$	$T_j = 25^{\circ}C$		1.6	2	v
▼ F		$V_{GE} = 0V$	$T_j = 150^{\circ}C$		1.5		v
+	D		$T_j = 25^{\circ}C$		125		
t <sub>rr</sub>	Reverse Recovery Time		$T_j = 150^{\circ}C$		220		ns
0	Devience Decession Change	$I_{\rm F} = 200 {\rm A}$	$T_j = 25^{\circ}C$		9		
Q <sub>rr</sub>	Reverse Recovery Charge	$V_{R} = 300V$ di/dt = 2800A/µs	$T_j = 150^{\circ}C$		20		μC
E.	Reverse Recovery Energy		$T_j = 25^{\circ}C$		2.2		T
Er			$T_j = 150^{\circ}C$		4.8		mJ
R <sub>thJC</sub>	Junction to Case Thermal Resistance					0.31	°C/W



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### Thermal and package characteristics

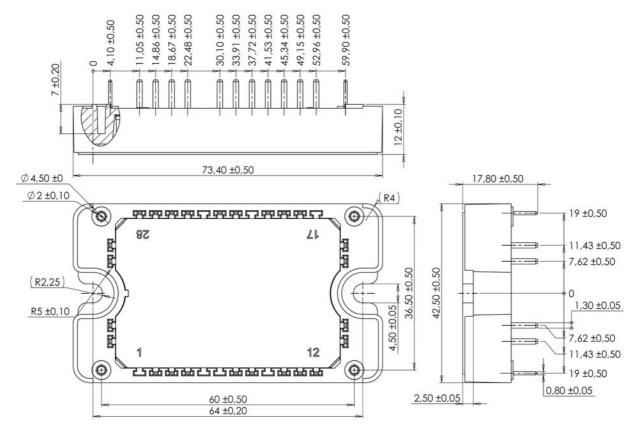
Symbol	Characteristic			Min	Max	Unit
VISOL	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
TJ	Operating junction temperature range			-40	175	
T <sub>JOP</sub>	Recommended junction temperature under switching conditions			-40	T <sub>J</sub> max -25	°C
T <sub>STG</sub>	Storage Temperature Range			-40	125	C
T <sub>C</sub>	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K			3952		K
$\Delta B/B$		$T_C = 100^{\circ}C$		4		%

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature  
R<sub>T</sub>: Thermistor value at T

### Package outline (dimensions in mm)



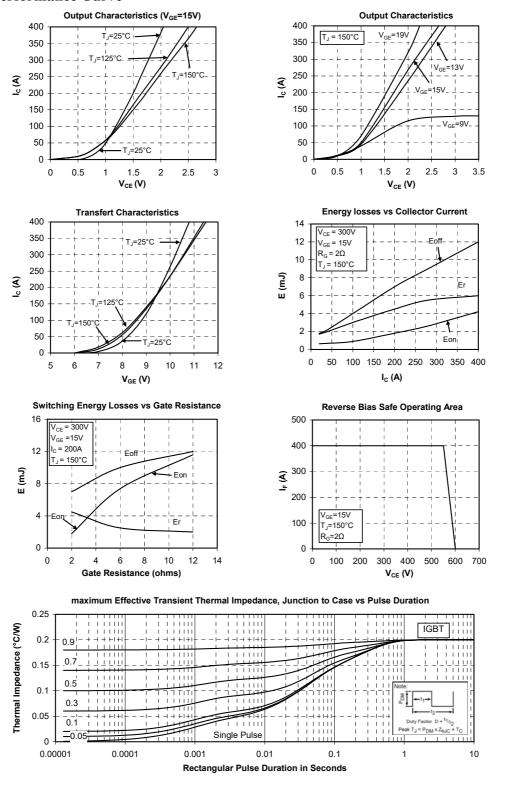
See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

www.microsemi.com

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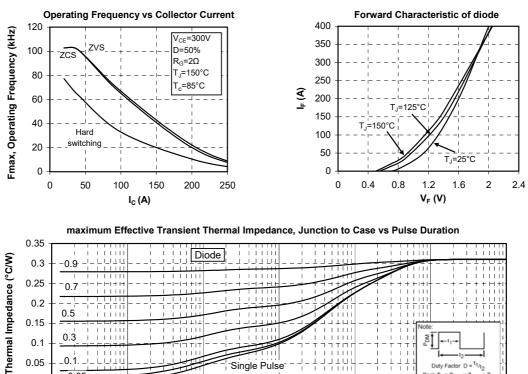
### **Typical Performance Curve**



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**Rectangular Pulse Duration in Seconds** 

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